

		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1531	SERIAL NO. 09/755,673		
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT Leonard Forbes et al.			
					FILING DATE January 5, 2001	GROUP 2823		
		U.S. PATENT DOCUMENTS						
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
K.N.	AA	5,605,857	02/97	Jost et al	437	760	Feb. 22, 1995	
K.N.	AB	5,985,731	11/99	Weng et al	438	396	Aug. 17, 1998	
K.N.	AC	6,395,650	05/02	Callegari et al	438	785	Oct. 23, 2000	
	AD							
	AE							
	AF							
	AG							
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	AI							
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	AK							
	AL							
FOREIGN PATENT DOCUMENTS								
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	AM						Yes	No
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	AO							
	AP							
	AQ							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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EXAMINER <i>Khrenengen</i>			DATE CONSIDERED 12/10/04					
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Form PTO-149		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531	SERIAL NO. 09/755,673		
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
K.N.	AM	JP200058777A	02/00	Japan - electronic translation and abstract			Yes <input checked="" type="checkbox"/> No <input type="checkbox"/>
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	AO						
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER	AR						
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<b>Khenguyen</b>				DATE CONSIDERED			12/10/04
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT-AND-TRADEMARK-OFFICE			ATTY. DOCKET NO. MI22-1531		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.			
					FILING DATE Filed Herewith		GROUP 2823	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
	AB						Yes	No
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
K.N.	AC	Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S.; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992						
	AD	Abstract of: Oxidation of lead films by rf sputter etching in an oxygen plasma; J.H. Greiner						
	AE	Abstract of: Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma; J.H. Greiner; Journal of Applied Physics; Vol. 42; Number 12; November 1971						
	AF	Abstract of: Measurement of Tunnel Current Density in a Metal Oxide Metal System as a Function of Oxide Thickness; J.M. Eldridge and J. Mailsoo						
	AG	Abstract of: Optical Measurement of Film Growth on Silicon and Germanium Surfaces in Room Air; R.J. Archer						
	AH	Preparation of Al-O-N Films by Electron Cyclotron Resonance Plasma-Assisted Chemical Vapor Deposition; Takashi Goto; Wei Zhang; Toshio Hirai, 1999 Publication Board, Japanese Journal of Applied Physics; Vol. 38 (1999) Pt. 1, No. 6A; pp. 3668-74						
	AJ	Ion assisted deposition of oxynitrides of aluminum and silicon; G.A. Al-Jumaily and T.A. Mooney; W.A. Spurgeon and H.M. Dauplaise						
K.N.	AJ	Abstract of: Preparation of aluminum nitride and oxynitride thin films by ion-assisted deposition; Targove, J.D.; Lingg, L.J.; Lehan, J.P. et al.; Conference: Materials Modification and Growth Using Ion Beams Symposium, pp. 311-16; Mater. Res. Soc., Pittsburgh, PA 1987						
EXAMINER <i>Khuennnayen</i>				DATE CONSIDERED 08/16/02				
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	AA							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
	AB						Yes	No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
K.N.	AC	Film Synthesis and Growth Using Energetic Beams; Material Research Society Symposium Proceedings Vol. 388; April 17-20, 1995 San Francisco, CA						
	AD	Some Properties of Chemically Vapor Deposited Films of $Al_2O_3$ on Silicon; E.A. Irene, V.J. Silvestri and G.R. Woolhouse; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 409-427						
	AE	Chemical Vapor Deposition of $Al_2O_3$ Films; V.J. Silvestri, E.A. Irene, S. Zirinsky, J.D. Kuprits; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 429-444						
	AF	Disk hydrogen plasma assisted chemical vapor deposition of aluminum nitride; T.Y. Sheng, Z.Q. Yu, and G.J. Collins; Appl. Phys. Lett. 52(7), February 1988; pp. 576-578						
	AG	Epitaxial Growth of Aluminum Nitride on Sapphire and Silicon; K. Dovidenko, S. Oktyabrsky, J. Narayan, and M. Razeghi; Mat. Res. Soc. Symp. Proc. Vol. 358; 1995 Materials Research Society; pp. 1023-1028						
	AH	III-Nitride, SiC and Diamond Materials for Electronic Devices; Materials Research Society, Symposium Proceedings Vol. 423; April 8-12, 1996, San Francisco, CA; pp. 667-672						
V K.N.	AI	Electrochemical Behaviour of AlN Films Prepared by Reactive Cathodic Sputtering; F. Vacando, Y. Massiant, P. Gravier, L. Fedrizzi and D. Brida; Materials Science Forum; Vols. 289-292 (1998) pp. 689-697; 1998 Trans Tech Publications, Switzerland						
V K.N.	AJ	Measurement of stress distribution in $Si_3N_4$ using AlN thin films; M. Akiyama, C.N. Xu, K. Nonaka, T. Watanabe; Journal of Materials Science Letters (1998) pp. 2093-2095						
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
	AC						Yes No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AD	Changes in optical transmittance and surface morphology of AlN thin films exposed to atmosphere; Yoshihisa Watanabe, Yoshifumi Sakuragi, Yoshiki Amamoto, and Yoshikazu Nakamura; J. Mater. Res., Vol 13, No. 10, Oct. 1998; 1998 Materials Research Society; pp. 2956-61					
	AE	Optical Interference Coatings; Flavin Abeles, Chair/Editor; Proceedings Europto Series; SPIE Vol. 2253; part 2 of 2; pp. 1275-85					
	AF	Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics; Ying Shi; Xiewen Wang; T.P. Ma; IEEE Electron Device Letters, Vol. 19, No. 10, October 1998; pp. 388-390					
	AG	High Quality Ultra-thin (1.5 nm) TiO <sub>x</sub> Si <sub>3</sub> N <sub>4</sub> Gate Dielectric for Deep Sub-micron CMOS Technology; Xin Guo, Xiewen Wang; Sizhong Luo, T.P. Ma, and T. Tamagawa; Dept. of Electrical Engineering, Yale University, New Haven, CT 06520					
	AH	High Quality Ta <sub>2</sub> O <sub>5</sub> Gate Dielectrics with $T_{\text{on}} < 10\text{Å}$ ; H. F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts and D.L. Kwong					
	AI	Abstract of: Low interface trap density for remote plasma deposited SiO <sub>x</sub> on n-type GaN; Applied Physics Letters, Vol. 68, No. 13; pp. 1850-2					
K.N.	AJ	Abstract of: Interface-state characteristics of GaN/GaAs MIS capacitors; Solid-State Electronics, vol. 25, no. 8, pp. 811-15					
EXAMINER Klemmagen		DATE CONSIDERED 08/16/02					
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	AA							
FOREIGN PATENT DOCUMENTS								
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	AB						Yes	No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
K.N.	AC	Applications of Aluminium Nitride Films Deposited by Reactive Sputtering to Silicon-on-Insulator Materials; Stefan Bengtsson, Mats Bergh, Manolis Choumas, Christian Olesen and Kjell O. Jeppson; Jpn. J. Appl. Phys. Vol. 35 (1996) Pt. 1, No. 8; pp. 4173-81						
	AD	Characteristics of AlN Thin Films Deposited by Electron Cyclotron Resonance Dual-Ion-Beam Sputtering and their Application to GHz-Bank Surface Acoustic Wave Devices; Hiroshi Okano, Naoki Tanaka, Yasuhiro Hiroo, Yasumi Kobayashi, Kenichi Shibata and Shoichi Nakano; Jpn. J. Appl. Phys. Vol. 33 (1994); Pt. 1, No. 3B; pp. 2957-2961						
	AE	An Aluminum Oxynitride Film; Wang Dehuang, Guo Liang; Thin Solid Films, 198 (1991) pp. 207-210						
	AF	Formation of aluminum oxynitride diffusion barriers for Ag metallization; Y. Wang and T. L. Alford; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; American Institute of Physics; pp. 52-54						
	AG	Abstract of: Simulation of Hyperthermal deposition of Si and C on SiC surfaces; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; 1999 American Institute of Physics						
	AH	Nitrogen plasma source ion implantation for corrosion protection of aluminum 6061-T4; J. H. Booske, L. Zhang, W. Wang, K. Mente, N. Zjaba, C. Baum, and J.L. Shohet; J. Mater. Res. Vol. 12, No. 5, May 1997; 1997 Materials Research Society; pp. 1356-66						
	AI	Thickness measurement of submonolayer native oxide films on silicon wafers; Fuhe Li, Marjorie K. Balazs, Bruce E. Deal; Wafers & Substrates; Solid State Technology, February 2000; pp. 87, 88, 92, 94, 96, 98						
K.N.	AJ	Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon; James Kolodzey et al.; IEEE Transactions on Electron Devices; Vol. 47, No. 1, January 2000; pp. 121-128						
EXAMINER	Khemunguyen			DATE CONSIDERED 08/16/02				
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K.N.	AC	Structural, Optical and Electronic Properties of Oxidized AlN Thin Films at Different Temperatures; Enam Ahmed Chowdhury et al.;				
	AD	Formation of Al-nitride films at room temperature by nitrogen ion implantation into aluminum; N. Lieske and R. Hezel; J. Appl. Phys. 52(9), Sept. 1981; pp. 5806-5810				
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EXAMINER <i>Khemanguyen</i>			DATE CONSIDERED 08/16/02			
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